
2SB1688

Silicon PNP Epitaxial
High voltage amplifier

HITACHI

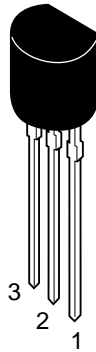
ADE-208-975A (Z)
2nd. Edition
Mar. 2001

Features

- High breakdown voltage
 $V_{CEO} = -300V$ min

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

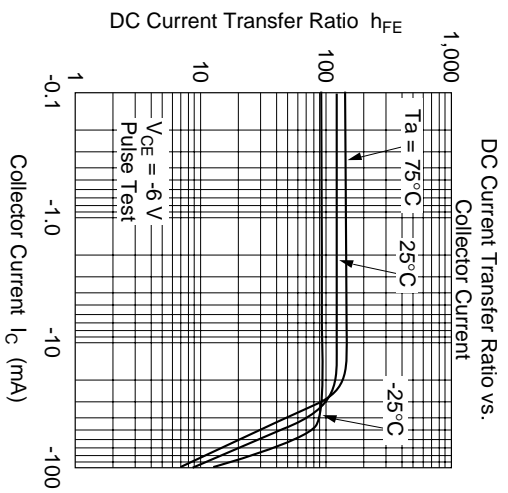
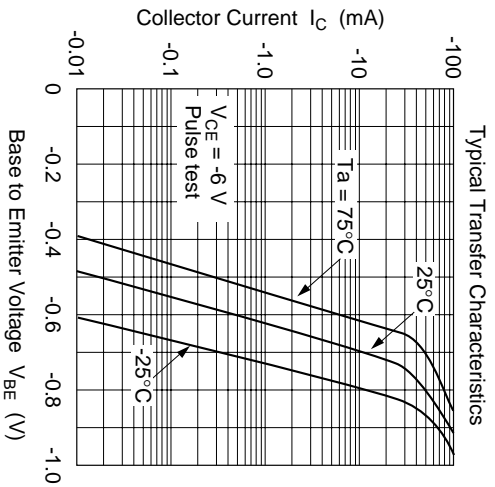
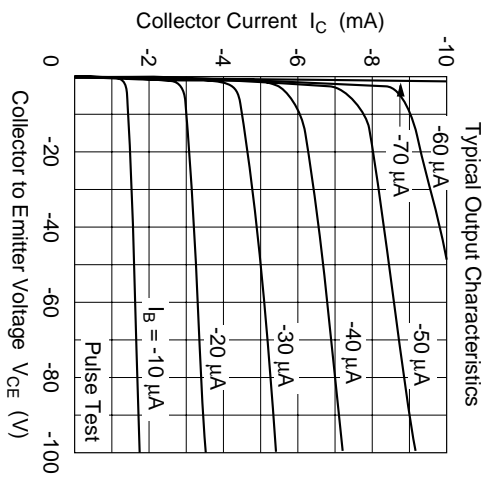
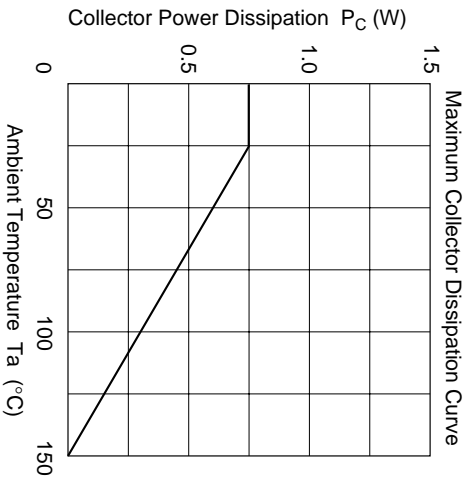
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| Item | Symbol | Ratings | Unit |
|------------------------------|------------------|-------------|------------------|
| Collector to base voltage | V_{CBO} | -300 | V |
| Collector to emitter voltage | V_{CEO} | -300 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Collector current | I_{C} | -50 | mA |
| Collector power dissipation | P_{C} | 750 | mW |
| Junction temperature | T_{j} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

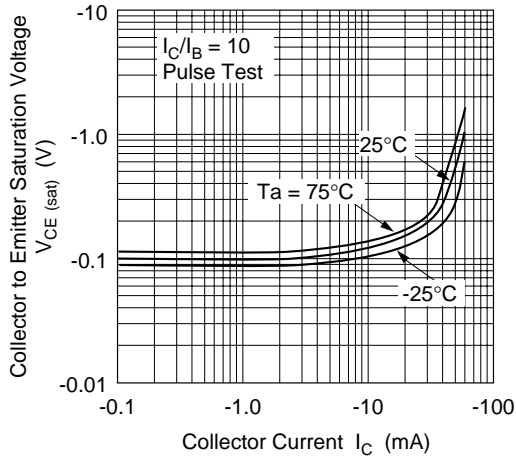
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|----------------------|-----|-----|-------|---------------|---|
| Collector cutoff current | I_{CBO} | — | — | -0.1 | μA | $V_{\text{CB}} = -300\text{V}, I_{\text{E}} = 0$ |
| | I_{CEO} | — | — | -0.1 | μA | $V_{\text{CE}} = -300\text{V}, R_{\text{BE}} = \infty$ |
| Emitter cutoff current | I_{EBO} | — | — | -10 | μA | $V_{\text{EB}} = -5\text{V}, I_{\text{C}} = 0$ |
| Base to emitter voltage | V_{BE} | — | — | -0.75 | V | $V_{\text{CE}} = -6\text{V}, I_{\text{C}} = -1\text{mA}$ |
| DC current transfer ratio | h_{FE} | 80 | — | 160 | — | $V_{\text{CE}} = -6\text{V}, I_{\text{C}} = -2\text{mA}$ |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | — | — | -0.9 | V | $I_{\text{C}} = -30\text{mA}, I_{\text{B}} = -3\text{mA}$ |

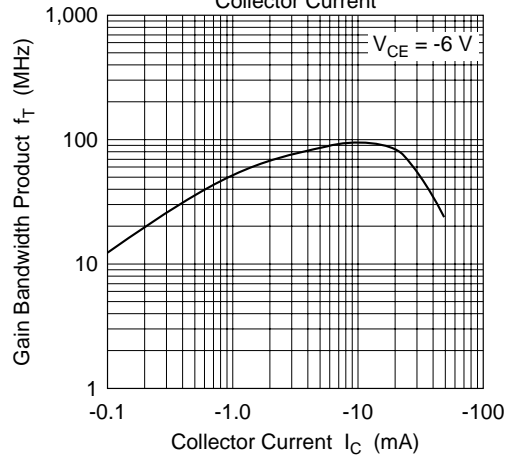
Main Characteristics



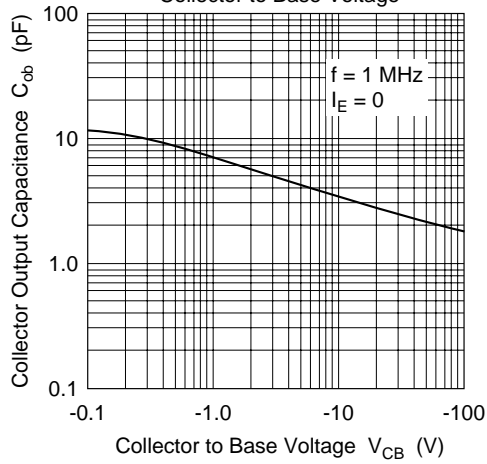
Collector to Emitter Saturation Voltage vs. Collector Current



Gain Bandwidth Product vs. Collector Current

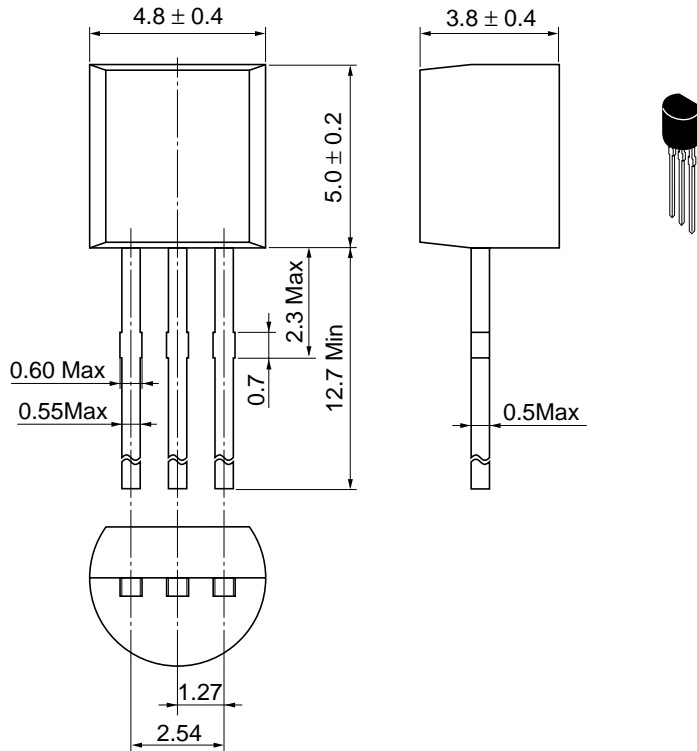


Collector Output Capacitance vs. Collector to Base Voltage



Package Dimensions

As of January, 2001
Unit: mm



| | |
|------------------------|-----------|
| Hitachi Code | TO-92 (1) |
| JEDEC | Conforms |
| EIAJ | Conforms |
| Mass (reference value) | 0.25 g |

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